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U. S. PATENT DOCUMENTS

*	DOCUMENT NUMBER	DATE	NAME	CLASS*	SUB-CLASS*	FILING DATE IF APPRO.
q1	5 7 2 5 6 7 4	3/10/98	Moustakas et al.	—	—	
1	6 0 5 1 8 4 9	4/18/00	Davis et al.	—	—	
	5 8 5 8 8 6 2	1/12/99	Westwater et al.	—	—	
	5 9 6 2 8 6 3	10/5/99	Russell et al.	—	—	
	5 3 8 1 7 5 3	1/17/95	Okajima et al.	—	—	
	6 0 6 3 2 4 6	5/16/00	Wolfe et al.	—	—	
	4 8 8 6 6 8 3	12/12/89	Hoke et al.	—	—	
	5 3 3 4 2 9 6	8/2/94	Henkens et al.	—	—	
	6 0 3 3 8 6 6	3/7/00	Guo et al.	—	—	
q1	5 9 2 2 1 8 3	7/13/99	Rauth	—	—	

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q1	2 0 8 6 1 2 1	3/27/90	Japan	Nishibe Toru et al.	—	—	
q1	1 1 1 7 7 1 3 4	7/2/99	Japan	Yamada Takeshi	—	—	

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Publication No. WO026422A1 for "HIGH PURITY GALLIUM FOR PREPARATION OF COMPOUND SEMICONDUCTOR, AND METHOD AND APPARATUS FOR PURIFYING THE SAME" by Yamamura et al., published on May 11, 2000;

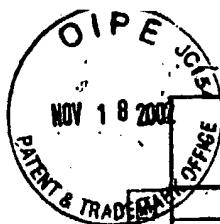
Publication No. WO9965068A1 for "FABRICATION OF GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL GROWTH FROM TRENCH SIDEWALLS" by Zheleva et al., published on December 16, 1999;

Publication No. WO9944224A1 for "METHOD OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL OVERGROWTH THROUGH MASKS, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY" by Davis et al., published on September 2, 1999;

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Y.F. Zhang, Y.H. Tang, N. Wang, C.S. Lee, I. Bello, S.T. Lee "ONE-DIMENSIONAL GROWTH MECHANISM OF CRYSTALLINE SILICON NANOWIRES", Journal of Crystal Growth 197 (1999) 136-140; 

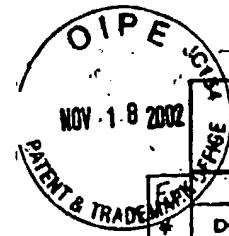
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A.M. Morales and C.M. Lieber "A LASER ABLATION METHOD FOR THE SYNTHESIS OF CRYSTALLINE SEMICONDUCTOR NANOWIRES", Science, Vol. 279, January 9, 1998, 208-211;

H.F. Yan, Y.J. Xing, Q.L. Hang, D.P. Yu, Y.P. Wang, J. Xu, Z.H. Xi, S.Q. Feng "GROWTH OF AMORPHOUS SILICON NANOWIRES VIA A SOLID-LIQUID-SOLID MECHANISM", Chemical Physics Letters 323 (2000) 224-228; *no date*

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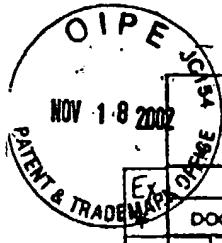


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*	DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS*	SUB-CLASS*	PERTINENT PAGES DWY SPEC
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<p>J.L. Gole and J.D. Stout, W.L. Rauch and Z.L. Wang "DIRECT SYNTHESIS OF SILICON NANOWIRES, SILICA NANOSPHERES, AND WIRE-LIKE NANOSPHERE AGGLOMERATES", Applied Physics Letters, Vol. 76, Number 17, 24 April 2000, 2346-2348;</p> <p>J. D. Holmes, K.P. Johnston, R.C. Doty, B. A. Korgel "CONTROL OF THICKNESS AND ORIENTATION OF SOLUTION-GROWN SILICON NANOWIRES", Science, Vol. 287, February 25, 2000, 1471-1473;</p> <p>P. Scheier, J. Marsen, M. Lonfat, W. Schneider, K. Sattler "GROWTH OF SILICON NANOSTRUCTURES ON GRAPHITE", Surface Science 458 (2000, 113-122; <i>no date</i></p> <p>D.P. Yu, Z.G. Bai, Y. Ding, Q.L. Hang, H.Z. Zhang, J.J. Wang, Y.H. Zou, W. Qian, G.C. Xiong, H.T. Zhou, and S.Q. Feng "NANOSCALE SILICON WIRES SYNTHESIZED USING SIMPLE PHYSICAL EVAPORATION", Applied Physics Letters, Vol. 72, Number 26, June 29, 1998, 3458-3460;</p>							

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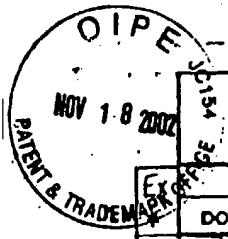
D.P. Yu, Y.J. Xing, Q.L. Hang, H.F. Yan, J. Xu, Z.H. Xi, S.Q. Feng "CONTROLLED GROWTH OF ORIENTED AMORPHOUS SILICON NANOWIRES VIA A SOLID-LIQUID-SOLID (SLS) MECHANISM", *Physica E* 9 (2001) 305-309; *ms date*

Lieber, "ONE-DIMENSIONAL NANOSTRUCTURES: CHEMISTRY, PHYSICS & APPLICATIONS",
Solid State Communications, Vol. 107, No. 11, 607-616; *no date*

Mr. M. M.

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